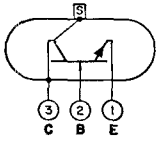
Noise Figure (with collector-to-emitter volts = 10, collector ma = 0.3, generator resistance = 510 ohms, circuit bandwidth = 1 cycle, and signal frequency = 1 kilocycle)	8 *max*	db

* Pulse duration = 300 μsec, duty factor = 0.018.

POWER TRANSISTOR



2N1768

Silicon n-p-n type used in a wide variety of intermediate-power switching and amplifier applications in industrial equipment requiring transistors having high voltage, current, and dissipation values. It is used in power switching, dc-to-dc converter, inverter, chopper, and relay actuating circuits; in voltage- and current-regulator circuits; and in dc and servo amplifier circuits. This type has an offset pedestal, stud-mount arrangement which provides positive heat-sink contact. Outline 19, Outlines Section. This type is electrically identical with type 2N1486 except for the following items:

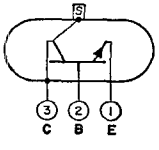
MAXIMUM RATINGS

COLLECTOR-TO-BASE VOLTAGE (with emitter open)	60 *max*	volts
COLLECTOR-TO-EMITTER VOLTAGE:		
With emitter-to-base volts = 1.5	60 *max*	volts
With base open	40 *max*	volts
TRANSISTOR DISSIPATION:		
At case temperatures up to 25°C	40 *max*	watts
At case temperatures above 25°C	See curve page 68	
LEAD TEMPERATURE (for 10 seconds maximum)	255 *max*	°C

CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage (with emitter-to-base volts = 1.5 and collector ma = 0.25)	60 *min*	volts
Collector-to-Emitter Sustaining Voltage (with collector ma = 100 and base current = 0)	40 *min*	volts
Thermal Resistance:		
Junction-to-case	4.375 *max*	°C/watt
Junction-to-ambient	175 *max*	°C/watt

POWER TRANSISTOR



2N1769

Silicon n-p-n type used in a wide variety of intermediate-power switching and amplifier applications in industrial equipment requiring transistors having high voltage, current, and dissipation values. It is used in power-switching, dc-to-dc converter, inverter, chopper, and relay actuating circuits; in voltage- and current-regulator circuits; and in dc and servo amplifier circuits. This type has an offset pedestal, stud-mount arrangement which provides positive heat-sink contact. Outline 19, Outlines Section. This type is identical with type 2N1486 except for the following items:

MAXIMUM RATINGS

TRANSISTOR DISSIPATION:		
At case temperatures up to 25°C	40 *max*	watts
At case temperatures above 25°C	See curve page 68	
LEAD TEMPERATURE (for 10 seconds maximum)	255 *max*	°C

CHARACTERISTICS

Thermal Resistance:		
Junction-to-case	4.375 *max*	°C/watt
Junction-to-ambient	175 *max*	°C/watt